



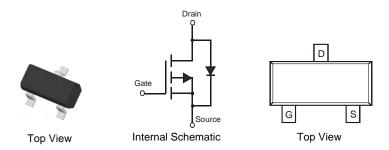
P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
 - $60m\Omega$ @ $V_{GS} = -4.5V$
 - 90mΩ @ V_{GS} = -2.5V
 - $113m\Omega$ @ $V_{GS} = -1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 (2)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



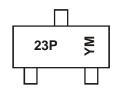
Ordering Information (Note 4)

Ī	Part Number	Qualification	Case	Packaging
	DMP2305U-7	Commercial	SOT23	3000/Tape & Reel
I	DMP2305UQ-7	Automotive	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



23P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

June 2012

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Maximum Ratings @T_A = 25°C unless otherwise specified

Characte	ristic		Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±8	V	
Continuous Drain Current (Note 5)	Steady State	T _A = 25°C T _A = 70°C	I _D	-4.2 -3.4	Α
Pulsed Drain Current (Note 6)			I _{DM}	-10	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	$R_{ heta JA}$	90	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

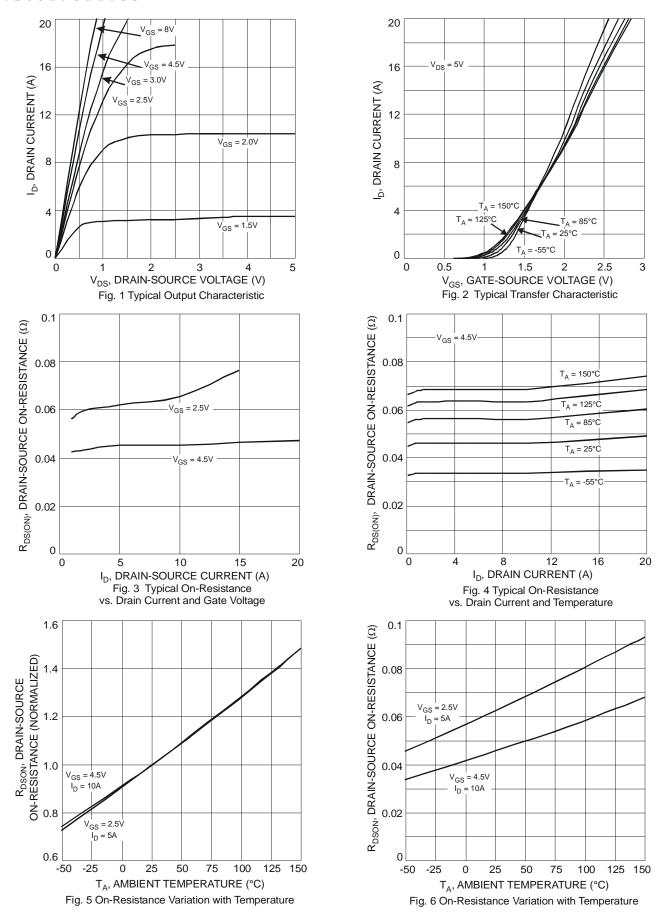
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20			V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(th)}	-0.5	-	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			45	60		$V_{GS} = -4.5V$, $I_D = -4.2A$		
Static Drain-Source On-Resistance	R _{DS (ON)}	_	60	90	mΩ	$V_{GS} = -2.5V$, $I_D = -3.4A$		
			87	113		$V_{GS} = -1.8V$, $I_D = -2.0A$		
Forward Transfer Admittance	Y _{fs}	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{iss}	_	727	_	pF	.,		
Output Capacitance	Coss	_	69	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	64	_	pF	1 = 1.001112		
Gate Resistance	R_{G}		23		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$		
SWITCHING CHARACTERISTICS								
Total Gate Charge		_	7.6	_	nC			
Gate-Source Charge	Q_{gs}	_	1.4	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -4V$, $I_{D} = -3.5A$		
Gate-Drain Charge	Q_{gd}	_	1.2	_	nC			
Turn-On Delay Time	t _{D(on)}	_	14.0	_	ns			
Turn-On Rise Time	t _r	_	13.0	_	ns	$V_{DS} = -4V$, $V_{GS} = -4.5V$,		
Turn-Off Delay Time	t _{D(off)}	_	53.8	_	ns	$R_L = 4\Omega$, $R_G = 6\Omega$, $I_D = -1A$		
Turn-Off Fall Time	t _f	_	23.2	_	ns			

Notes:

- 5. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width t \leq 10s. 6. Repetitive rating, pulse width limited by junction temperature. 7. Short duration pulse test used to minimize self-heating effect.







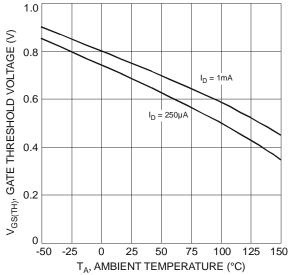
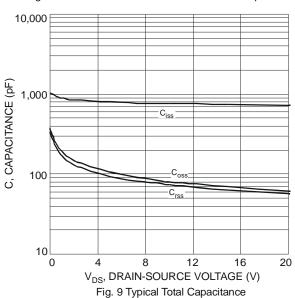
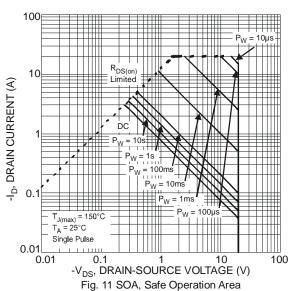
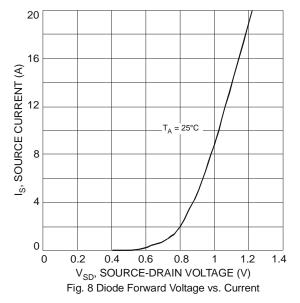


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







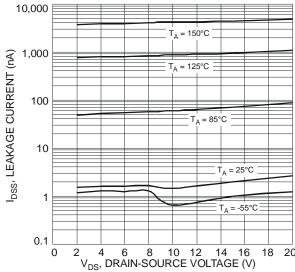
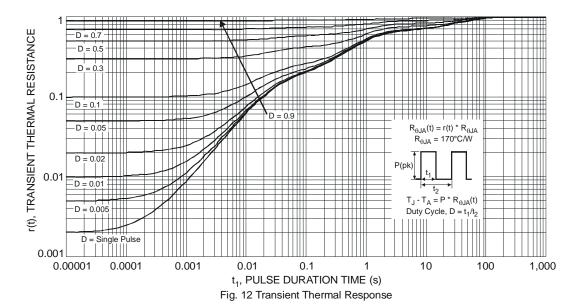
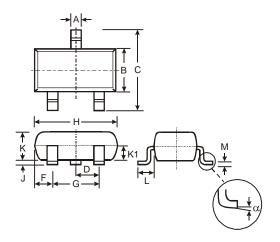


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage



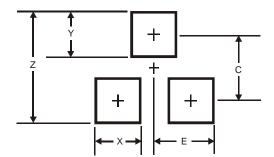


Package Outline Dimensions



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
٦	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)			
Z	2.9			
Х	0.8			
Y	0.9			
С	2.0			
E	1.35			



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